# imall

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#### N-CHANNEL ENHANCEMENT MODE FIELD MOSFET

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
001/	3.0Ω @ V <sub>GS</sub> = 10V	400mA
60V	4.0Ω @ V <sub>GS</sub> = 5V	330mA

#### **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
  Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

#### **Features and Benefits**

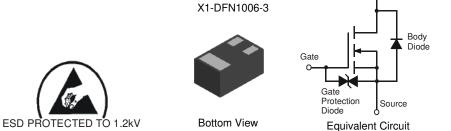
- N-Channel MOSFET
- Low On-Resistance
- Low Gate-Threshold Voltage
- Low-Input Capacitance
- Fast Switching Speed
- Small-Surface Mount Package
- ESD Protected Gate, 1.2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

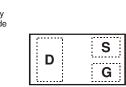
#### **Mechanical Data**

• Case: X1-DFN1006-3

Drain

- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208@4
- Weight: 0.001 grams (Approximate)





Top View Pin Configuration

#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN65D8LFB-7	X1-DFN1006-3	3,000/Tape & Reel
DMN65D8LFB-7B	X1-DFN1006-3	10.000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

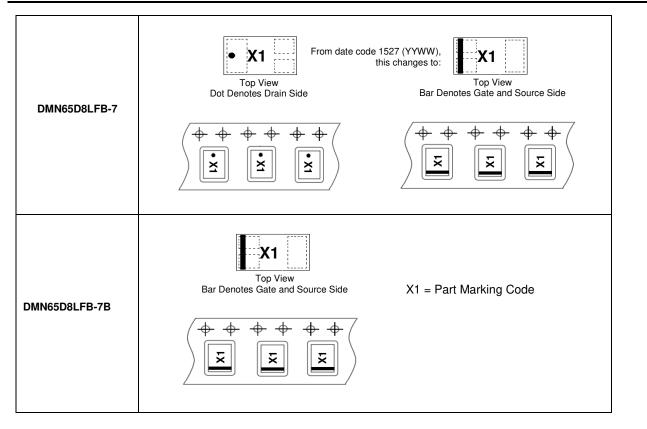
 See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Haloger- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com.



### **Marking Information**





#### **Maximum Ratings**

Characteristic	Symbol	Value	Units		
Drain-Source Voltage			V <sub>DSS</sub>	60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 4) $V_{GS}$ = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	260 210	mA
Continuous Drain Current (Note 5) $V_{GS}$ = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	400 310	mA

#### **Thermal Characteristics**

Characteristic	Symbol	Value	Units
Power Dissipation, @T <sub>A</sub> = +25°C (Note 4)	PD	430	mW
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 4)	$R_{ extsf{ heta}JA}$	290	°C/W
Power Dissipation, $@T_A = +25^{\circ}C$ (Note 5)	PD	840	mW
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 5)	$R_{ heta}JSA$	147	°C/W
Operating and Storage Temperature Range	TJ, T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

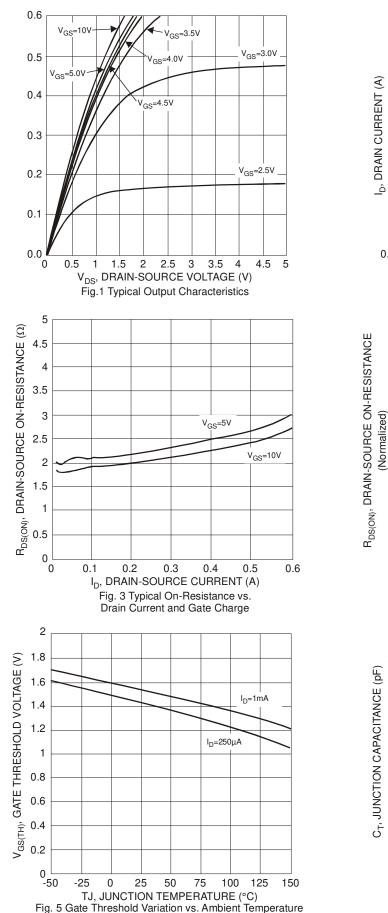
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	-	0.1	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Body Leakage	IGSS	-	-	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)					•		
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.2	-	2.0	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Passa			3.0	Ω	$V_{GS} = 10V, I_D = 0.115A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	-	-	4.0	12	$V_{GS} = 5V, I_D = 0.1115A$	
Forward Transfer Admittance	Y <sub>fs</sub>	80	320	-	mS	$V_{DS} = 10V, I_D = 0.115A$	
Diode Forward Voltage	V <sub>SD</sub>	-	0.7	1.2	V	$V_{GS} = 0V, I_S = 0.115A$	
DYNAMIC CHARACTERISTICS (Note 7)			•		•		
Input Capacitance	Ciss	-	25	-	pF		
Output Capacitance	Coss	-	4.7	-	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	-	2.5	-	pF	1	
Turn-On Delay Time	t <sub>D(on)</sub>	-	3.27	-	ns		
Turn-On Rise Time	tr	-	3.15	-	ns	$V_{DD} = 30V, V_{GEN} = 10V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	12.025	-	ns	$R_{GEN} = 25\Omega, I_D = 0.115A$	
Turn-Off Fall Time	t <sub>f</sub>	-	6.29	-	ns		

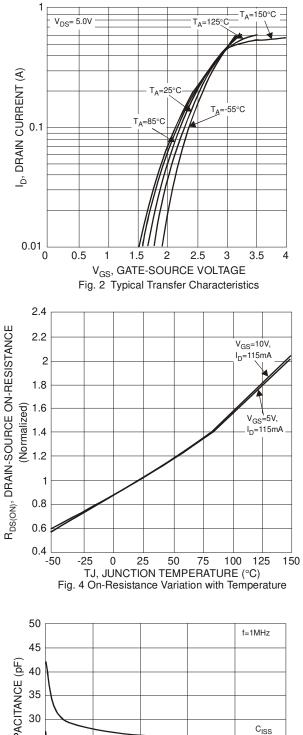
Notes: 4. Device mounted on FR-4 PCB with minimum recommended pad layout, single-sided.

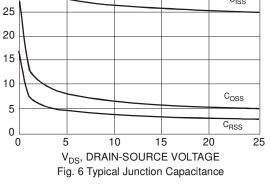
Device mounted on 1"x 2" FR-4 PCB with high coverage 2oz. Copper, single-sided.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

#### DMN65D8LFB

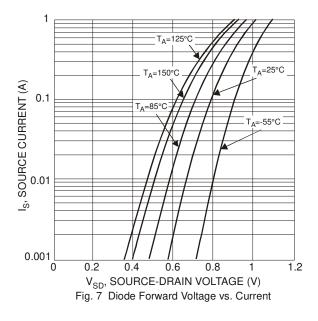






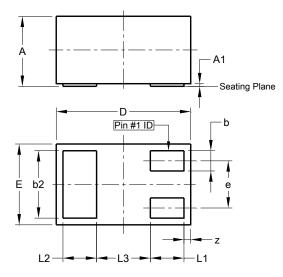






## Package Outline Dimensions

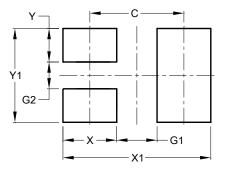
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



Х	X1-DFN1006-3				
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
E	0.55	0.675	0.60		
е	1	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	1	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					

#### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70

DMN65D8LFB Document number: DS35545 Rev. 4 - 2



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